

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	171	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:47
L2	0	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and delinit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:47
L3	0	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and delimit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:48
L4	28	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and (limit or boundary) near9 memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:48
L5	11	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and (limit or boundary) near9 memory and anisotropic and (wet near etch\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:49
L6	9	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and (limit or boundary) near9 memory and anisotropic and (wet near etch\$4) and (tunnel near oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:54
L7	9	nonvolatile and (sidewall near9 polysilicon) and ((oxide or dielectric or insulat\$4) near9 (word near line)) and (limit or boundary) near9 memory and anisotropic and (wet near etch\$4) and (tunnel near oxide) and (ion near implant\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:54

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S1	4	((("5753953") or ("6011725") or ("6215148B1") or ("6271090B1") or ("9312352A") or ("EP1170800A2")). PN. or (WO01/17030A1).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2007/04/25 13:15
S2	2	S1 and nonvolatile	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:16
S3	0	S1 and nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:17
S4	1104	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:17
S5	261	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:18
S6	211	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier)) and (first near9 (insulat\$4 or oxide or dielectric)) and (second near9 (insulat\$4 or oxide or dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:20
S7	12	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier)) and (first near9 (insulat\$4 or oxide or dielectric)) and (second near9 (insulat\$4 or oxide or dielectric)) and (pattern near9 mask) and ((side near wall) near9 mask) and source and drain and (third near9 (insulat\$4 or oxide or dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:22

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S8	6	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier)) and (first near9 (insulat\$4 or oxide or dielectric)) and (second near9 (insulat\$4 or oxide or dielectric)) and (pattern near9 mask) and ((side near wall) near9 mask) and source and drain and (third near9 (insulat\$4 or oxide or dielectric)) and (control near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:23
S9	1	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier)) and (first near9 (insulat\$4 or oxide or dielectric)) and (second near9 (insulat\$4 or oxide or dielectric)) and (pattern near9 mask) and ((side near wall) near9 mask) and source and drain and (third near9 (insulat\$4 or oxide or dielectric)) and (control near layer) and (word near line)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 13:24
S10	7	nonvolatile and ((insulat\$4 or oxide or dielectric) near9 (storage near4 layer)) and (mask near9 (substrate or semiconductor or wafer or carrier)) and (first near9 (insulat\$4 or oxide or dielectric)) and (second near9 (insulat\$4 or oxide or dielectric)) and (pattern near9 mask) and ((side near wall) near9 mask) and source and drain and (third near9 (insulat\$4 or oxide or dielectric)) and (polysilicon or metal or siliconiz\$4) and (word near line)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:10
S11	1638	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:11
S12	365	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide) near9 ((silicon near oxide) or (silicon near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:12

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S13	58	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide) near9 ((silicon near oxide) or (silicon near nitride)) near9 (dielectric or insulat\$4 or oxide) near9 (control or polysilicon or metal or siliconiz\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:26
S14	41	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide) near9 ((silicon near oxide) or (silicon near nitride)) near9 (dielectric or insulat\$4 or oxide) near9 (control or polysilicon or metal or siliconiz\$4) and tunnel\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:29
S15	9	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide) near9 ((silicon near oxide) or (silicon near nitride)) near9 (dielectric or insulat\$4 or oxide) near9 (control or polysilicon or metal or siliconiz\$4) and tunnel\$4 and (side near wall)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:27
S16	19	nonvolatile and (substrate or wafer or semiconductor or carrier) near9 (silicon near dioxide) near9 ((silicon near oxide) or (silicon near nitride)) near9 (dielectric or insulat\$4 or oxide) near9 (control or polysilicon or metal or siliconiz\$4) and tunnel\$4 and mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:31
S17	852	nonvolatile and (sidewall near9 mask)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:32
S18	63	nonvolatile and (sidewall near9 mask) and ((charge near storage) near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:32
S19	63	nonvolatile and (sidewall near9 mask) and ((charge near storage) near layer) and (oxide or dielectric or insulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:33

## EAST Search History

S20	30	nonvolatile and (sidewall near9 mask) and ((charge near storage) near layer) and (oxide or dielectric or insulat\$4) and (word near line) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:40
S21	64	nonvolatile and (delimit\$4 near9 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:41
S22	26	nonvolatile and (delimit\$4 near9 memory) and (oxide or dielectric or insulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:41
S23	26	nonvolatile and (delimit\$4 near9 memory) and (oxide or dielectric or insulat\$4) and (polysilicon or control or metal or siliconiz\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:42
S24	4	nonvolatile and (delimit\$4 near9 memory) and (oxide or dielectric or insulat\$4) and (polysilicon or control or metal or siliconiz\$4) and (charge near storage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:43
S25	5	nonvolatile and (delimit\$4 near9 memory) and (oxide or dielectric or insulat\$4) and (polysilicon or control or metal or siliconiz\$4) and (storage near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 14:44
S26	5	nonvolatile and (delimit\$4 near9 memory) and (storage near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/26 09:46

## EAST Search History

S27	513	"6011725"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/25 15:00
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